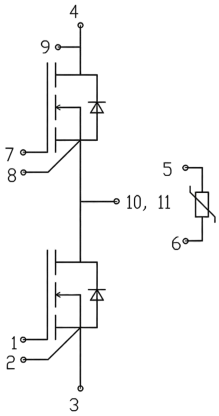
EconoDUAL3 Half Bridge SiC Module

Parameter	Value	Unit
V_{DS}	1200	V
I_D	1000	A
$R_{DS(ON)}$	1.3	mΩ
Q_G	2384	nC





Features:

- Ultra Low Loss
- High-frequency Operation
- High Temperature, Humidity, and Bias Operation
- Zero Turn-off Tail Current from MOSFET

Applications:

- Motor Drives
- Servo Drives
- UPS Systems
- Wind Turbines
- High-Power Converters

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-source Voltage	1200	V
V_{GS}	Gate-source Voltage (dynamic)	-10/+22	V
I_D	Drain Current (continuous)	1000	A
I_{DM}	Drain Current (pulsed)	2000	A
T_{op};T_{stg}	Operating and Storage Temperature Range	-40 to +175	°C
T_J	Junction Temperature	175	°C
L_{Stray}	Stray Inductance	20	nH
V_{isol}	Isolation Test Voltage (DC; 2mA; t=10s)	4.2	kV
$R_{th(j-c)}$	Thermal Resistance, Junction-to-heatsink	0.12	°C/W

MOSFET Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics (at T_C=25°C unless otherwise specified)						
B_{VDS}	Drain-source Breakdown Voltage	1200	-	-	V	V_{GS}=0V
I_{DSS}	Zero Gate Voltage Drain Current	-	-	400	μA	V_{DS}=1200V; V_{GS}=0V
I_{GSS}	Gate-body Leakage Current	-	-	4.0	μA	V_{GS}=-10/20V; V_{DS}=0V
$V_{GS(th)}$	Gate Threshold Voltage	2.0	-	4.0	V	V_{DS}=V_{GS} ; I_D=80mA
$R_{DS(on)}$	Static Drain-source on Resistance	-	1.3	1.6	mΩ	V_{GS}=18V; I_D=600A
$V_{GS(on)}$	Recommended Turn-on Voltage	-	18	-	V	Static
$V_{GS(off)}$	Recommended Turn-off Voltage	-	-5	-	V	
R_G	Gate Resistance	-	1.5	-	Ω	V_{AC}=25mV; f=1MHz

Dynamic characteristics (at T_C=25°C unless otherwise specified)						
C_{iss}	Input Capacitance	-	63.8	-	nF	V_{DS}=1000V; f=100kHz; V_{AC}=25mV
C_{oss}	Output Capacitance	-	2.5	-		
C_{rss}	Reverse Transfer Capacitance	-	128	-	pF	
E_{on}	Turn-on Energy	-	40.3	-	mJ	V_{DS}=600V; V_{GS}=-5/+18V; I_D=1000A; Load=50μH,$R_{G(ext)}$=5Ω
E_{off}	Turn-off Energy	-	95.4	-		
Q_{GS}	Gate-source Charge	-	656	-	nC	V_{DD}=800V; V_{GS}=-5/+18V; I_D=600A
Q_{GD}	Gate-drain Charge	-	786	-		
Q_G	Total Gate Charge	-	2384	-		
$t_{d(on)}$	Turn-on Delay Time	-	174	-	ns	V_{DS}=600V; V_{GS}=-5/+18V; I_D=1000A; Load=50μH,$R_{G(ext)}$=5Ω
t_r	Rise Time	-	162	-		
$td_{(off)}$	Turn-off Delay Time	-	567	-		
t_f	Fall Time	-	212	-		

Body Diode Characteristics (T_J =25°C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
V_{FSD}	Forward Voltage	-	3.2	6	V	V_{GS}=0V; I_F=600A
I_S	Continuous Diode Forward Current	-	600	-	A	V_{GS}=0V; T_C=25°C
T_{RR}	Reverse Recovery Time	-	93	-	ns	V_{GS}=-5/+18V; I_F=1000A V_R=600V; Load=50μH $R_{G(ext)}$=5Ω
Q_{RR}	Reverse Recovery Charge	-	6376	-	nC	
I_{RRM}	Peak Reverse Recovery Current	-	290	-	A	

NTC Thermistor Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
R_{25}	Rated Resistance	-	5.00	-	kΩ	T_{NTC}=25°C
ΔR/R	Deviation of R_{100}	-5	-	5	%	T_{NTC}=25°C; R_{100}=493.3Ω
$B_{25/50}$	Beta Value for 25°C to 50°C	-	3375	-	K	R_2=R_{25} exp[$B_{25/50}$(1/T2-1/(298.15K))]
$B_{25/80}$	Beta Value for 25°C to 80°C	-	3414	-	K	R_2=R_{25} exp[$B_{25/80}$(1/T2-1/(298.15K))]
$B_{25/100}$	Beta Value for 25°C to 100°C	-	3436	-	K	R_2=R_{25} exp[$B_{25/100}$(1/T2-1/(298.15K))]

Typical Characteristics

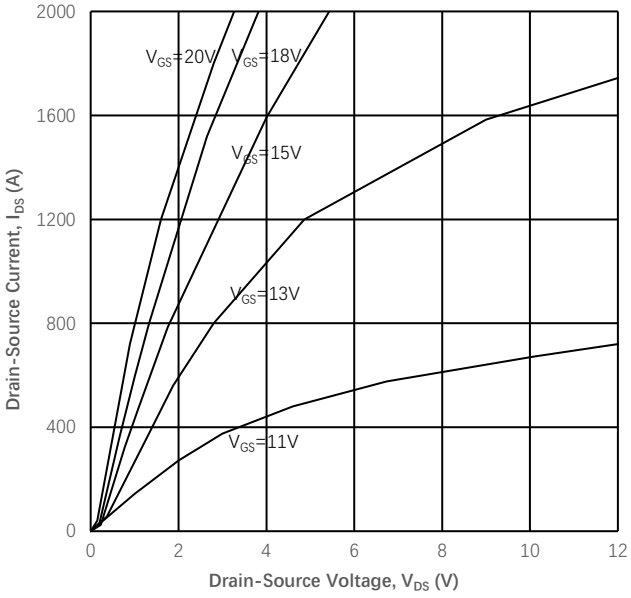


Figure 1

Output Characteristics (T_J=25 °C)

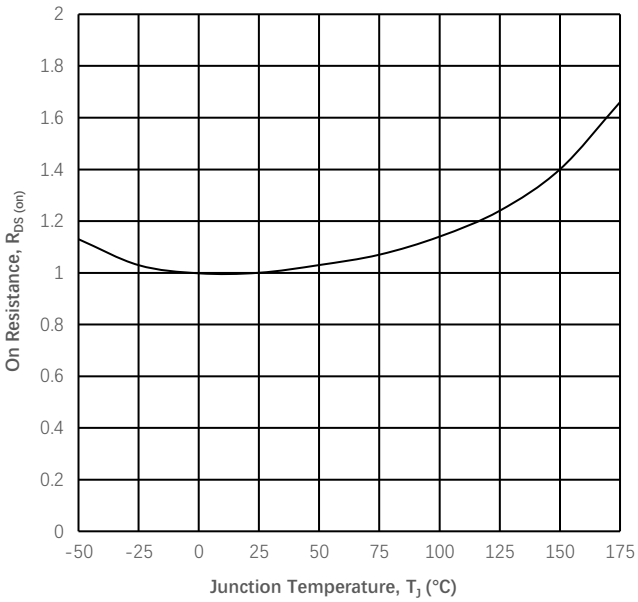


Figure 2

Normalized On-Resistance vs. Temperature

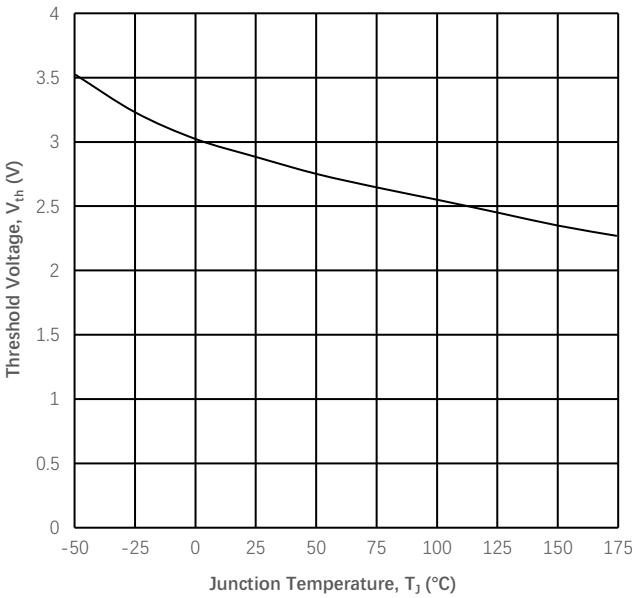


Figure 3

Threshold Voltage vs. Temperature

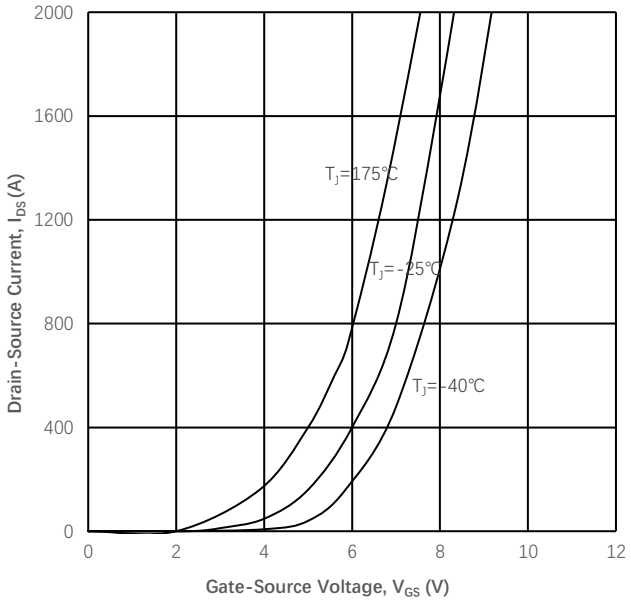


Figure 4

Transfer Characteristic for Various T_J

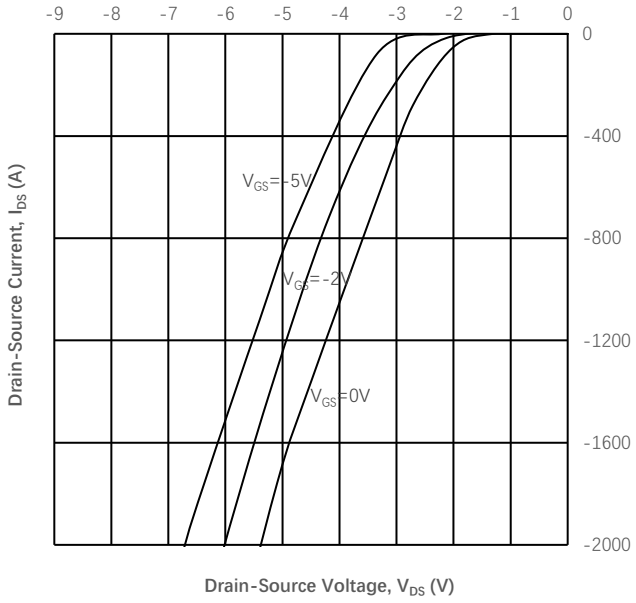


Figure 5

Diode Characteristic at 25 ˚C

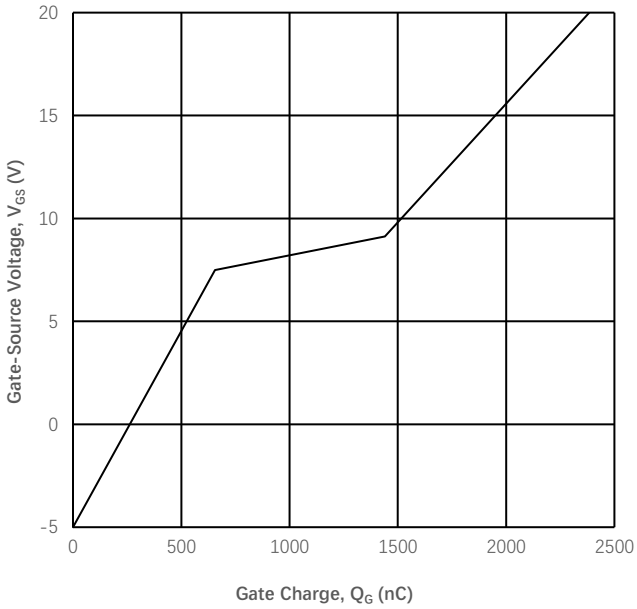


Figure 6

Typical Gate Charge Characteristics

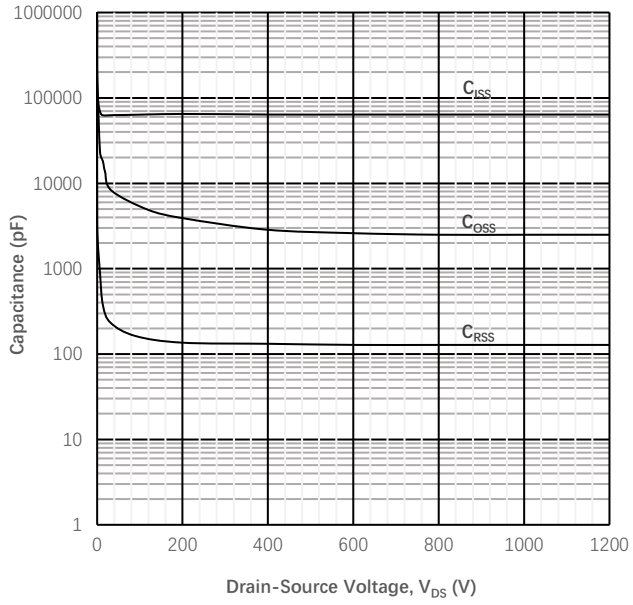


Figure 7

Typical Capacitances vs. Drain-Source Voltage

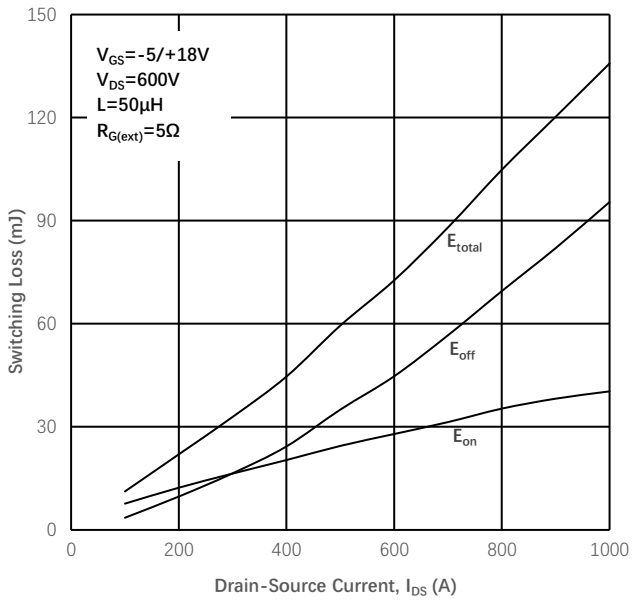


Figure 8

Inductive Switching Energy vs. Drain Current

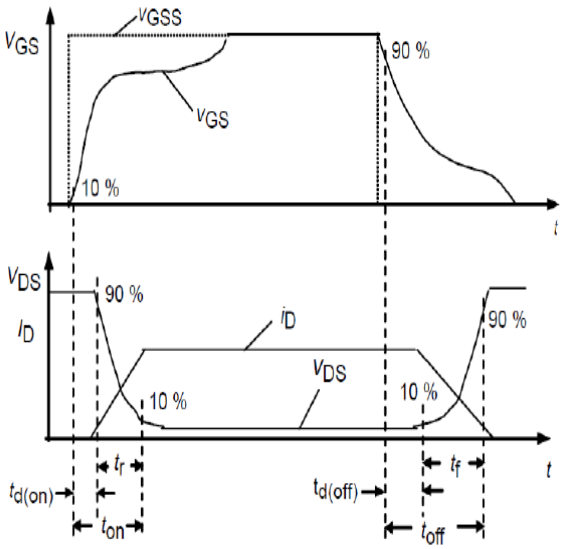


Figure 9
Switching Time Description

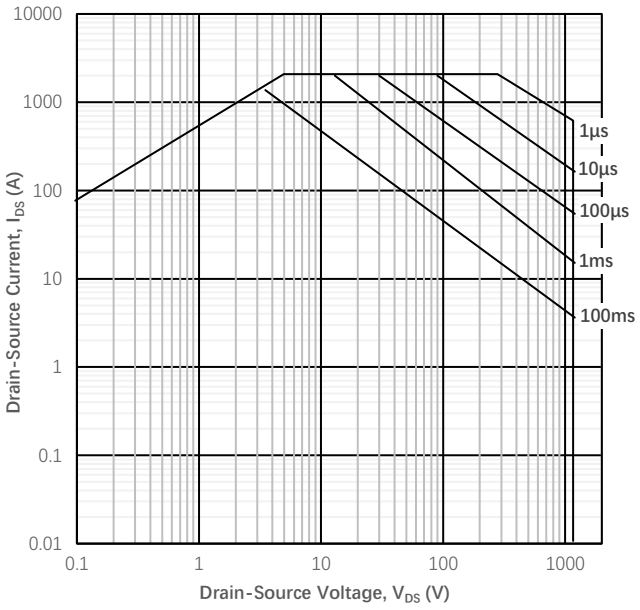
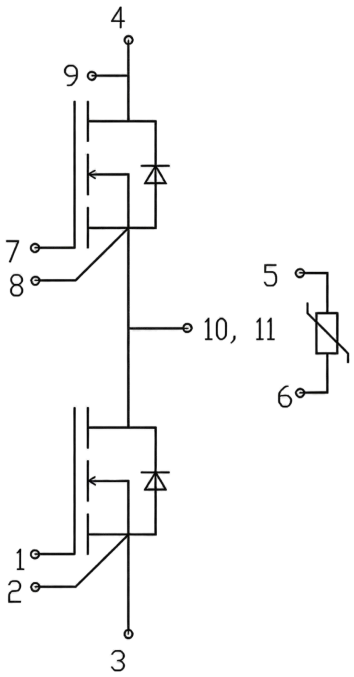
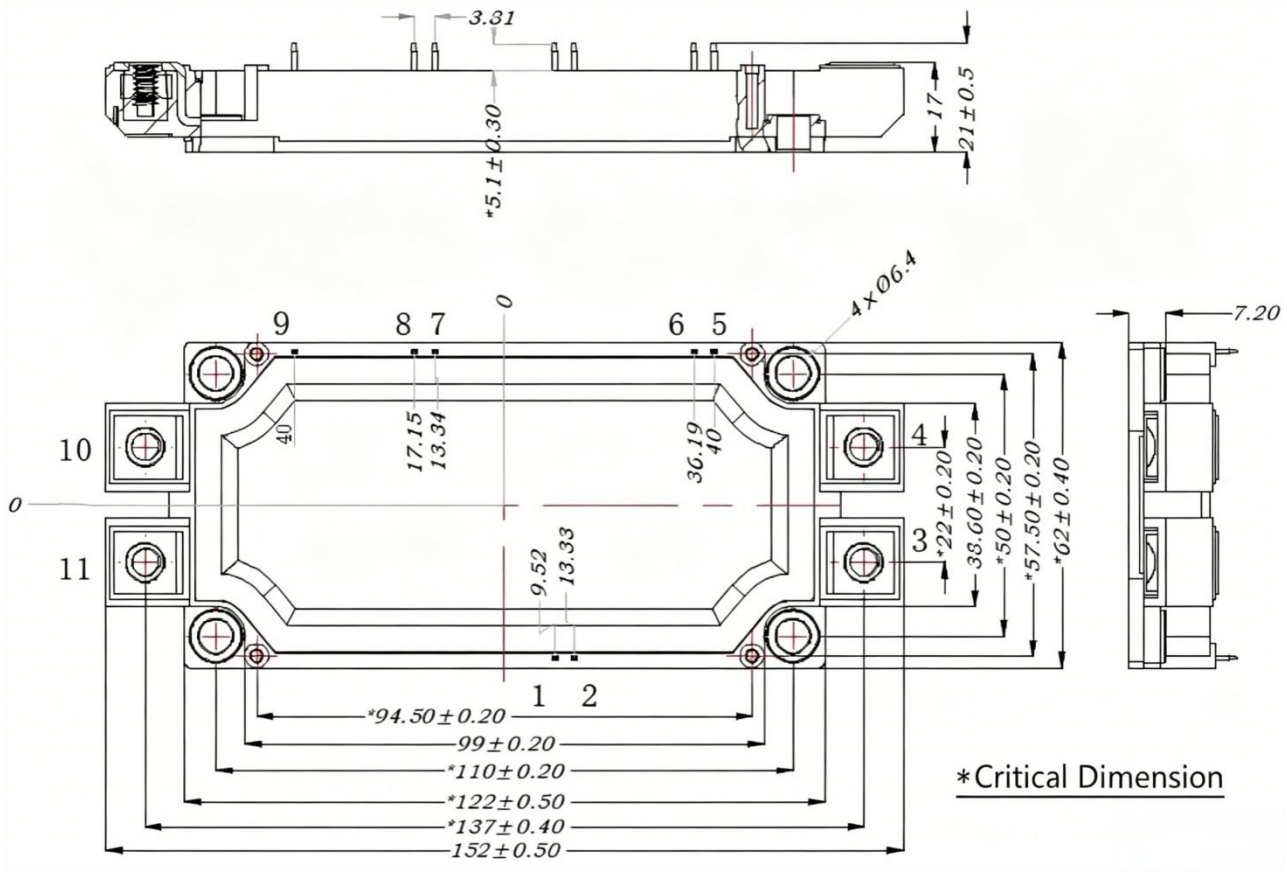


Figure 10
Safe Operating Area

Circuit Diagram



Package Outlines(Unit: mm):



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